TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

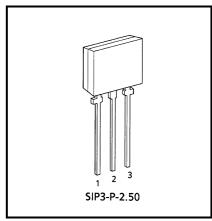
TPD1024AS

Low-Side Power Switch for Motors, Solenoids, and Lamp Drivers

TPD1024AS is a monolithic power IC for low-side switches. The IC has a vertical MOS FET output which can be directly driven from a CMOS or TTL logic circuit(e.g, an MPU). The device offers intelligent selfprotection function.

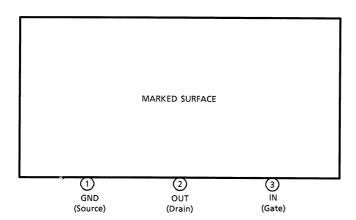
Features

- A monolithic power IC with a new structure combining a control block and a vertical power MOS FET(π -MOS) on a single chip.
- Can directly drive a power load from a CMOS logic.
- Built-in protection against overvoltage, load short circuiting, and thermal shutdown.
- Low on resistance : RDS (ON) = 0.5 Ω (max) (@VIN = 5 V, T_j = 25°C)
- Package : TPS Can be packed in tape.



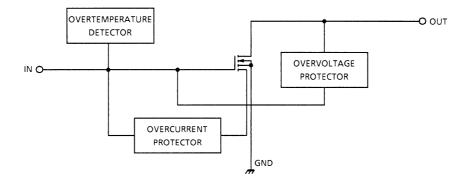
Weight: 0.54g (typ.)

Pin Assignment



Note: That because of its MOS structure, this product is sensitive to static electricity.

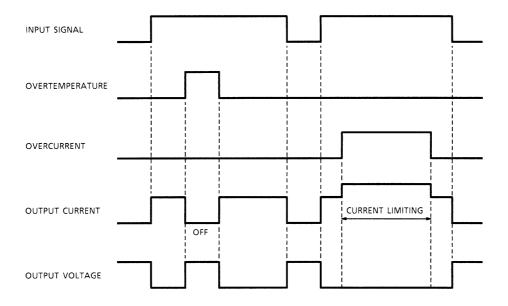
Block Diagram



Pin Description

Pin No.	Symbol	Function
1	GND	Ground pin.
2	OUT	Output pin. When current in excess of the typical current (3.5 A (typ.)) flows to the output pin, the current limiter operates to protect the IC.
3	IN	Input pin. Input is CMOS-compatible, with pull-down resistor connected. Even if the input is open, output will not accidentally turn on.

Timing Chart



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Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V _{DS (DC)}	40	V
Output current	I _D	1.5	Α
Input voltage	V_{GS}	- 0.5 to 6	V
Power dissipation	P _D	1.2	W
Operating temperature	T _{opr}	- 40 to 85	°C
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	- 55 to 150	°C

Recommendable Condition

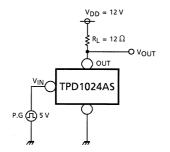
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Input voltage	V _{IN}	_	4.5	5	6	٧

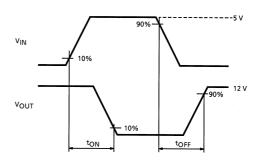
Electrical Characteristics (Tj = 25°C)

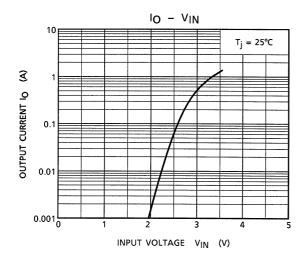
Characteristic	Symbol	Test Cir- cuit	Test Condition	Min	Тур.	Max	Unit
Drain-source breakdown voltage	V (BR) DSS	_	V _{GS} = 0, I _D = 10 mA	40	_	_	V
Operating supply voltage	V _{DD} (OPR)	_	_	_	_	18	V
Current at output off	I _{DSS (1)}	_	V _{GS} = 0, V _{DS} = 40 V	_	_	3	mA
Current at output off	I _{DSS (2)}	_	V _{GS} = 0, V _{DS} = 24 V	_	_	100	μΑ
Input threshold voltage	V _{th}	_	V _{GS} = 10 V, I _D = 1 mA	0.8	_	2.5	V
Input current	I _{GSS}	_	V _{GS} = 5 V, at normal operation	_	_	300	μA
On resistance	R _{DS (ON)}	_	V _{GS} = 5 V, I _D = 1 A	_	_	0.5	Ω
Thermal shutdown temperature	T _S	_	_	_	160	_	°C
Overcurrent protection	IS	_	V _{DS} = 12 V, V _{GS} = 5 V	_	3.5	_	Α
Cuitabia a tiesa	toN	_	1 $V_{DS} = 12 \text{ V}, V_{GS} = 5 \text{ V},$ $R_L = 12\Omega$	_	50	_	μs
Switching time	toff	7 7		_	10	_	μs
Diode forward voltage Between drain and source	V _{DSF}	_	I _F = 1.5 A	_	0.9	1.8	٧
Avalanche energy	E _A	_	L = 10 mH, Single pulse	30	_	_	mJ

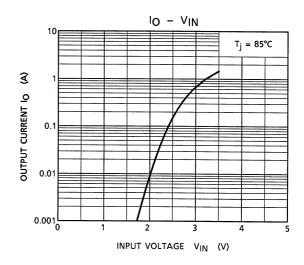
Test Circuit 1

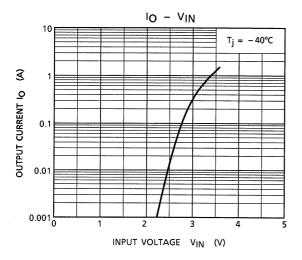
Switching Time

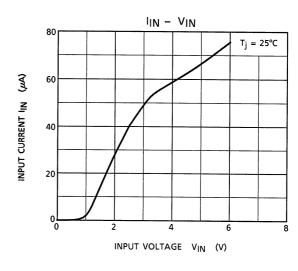


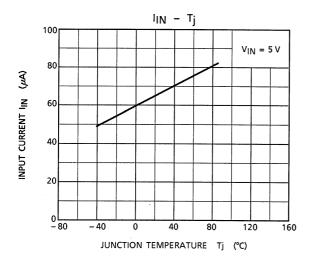


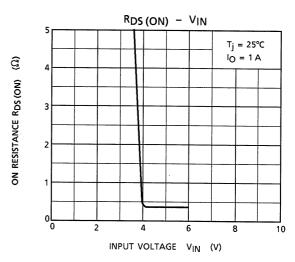


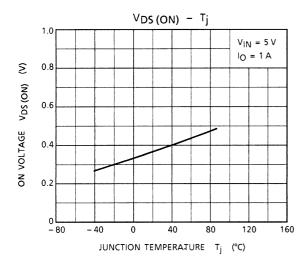


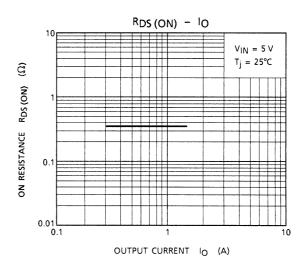


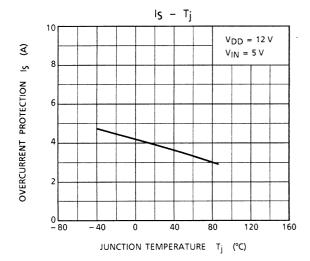


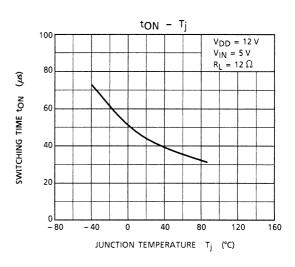


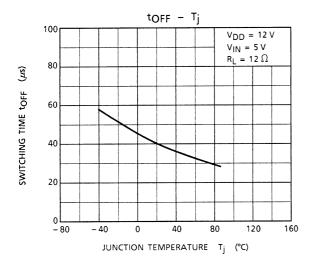


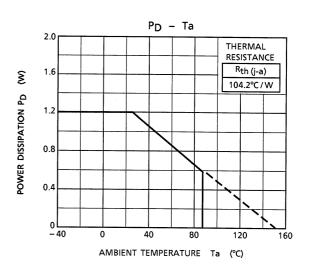








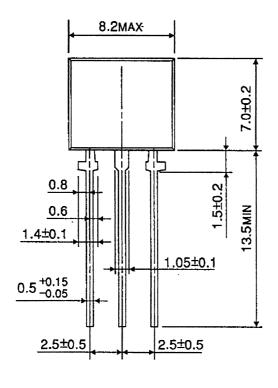


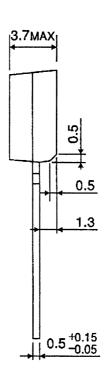


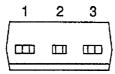
Unit: mm

Package Dimensions

SIP3-P-2.50







Weight: 0.54g (typ.)

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